



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diode

B5818WS SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 1 A

Collector-base voltage

V_R : 30 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

MARKING: SK

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\text{mA}$	30		V
Reverse voltage leakage current	I_R	$V_R = 30\text{V}$		1	mA
Forward voltage	V_F	$I_F = 1\text{A}$ $I_F = 3\text{A}$		0.55 0.875	V
Diode capacitance	C_D	$V_R = 4\text{V}, f = 1\text{MHz}$		120	pF

